
2SK1575

Silicon N-Channel MOS FET

HITACHI

Application

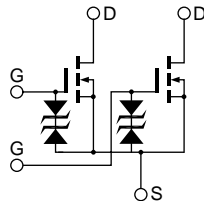
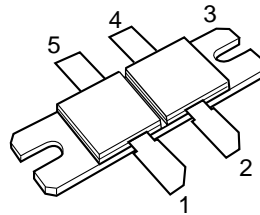
VHF amplifier

Features

- High gain, high efficiency
PG = 13 dB, $\eta_D = 65\%$ typ ($f = 190$ MHz)
- Compact package
Suitable for push - pull circuit

Outline

RFPK-B



1. Drain
2. Drain
3. Source
4. Gate
5. Gate

Absolute Maximum Ratings (Ta = 25°C)

| Item | Symbol | Ratings | Unit |
|-------------------------|-------------------|-------------|------|
| Drain to source voltage | V_{DSS} | 180 | V |
| Gate to source voltage | V_{GSS} | ±20 | V |
| Drain current | I_D | 16 | A |
| Channel dissipation | Pch* ¹ | 200 | W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Note: 1. Value at T_c = 25°C

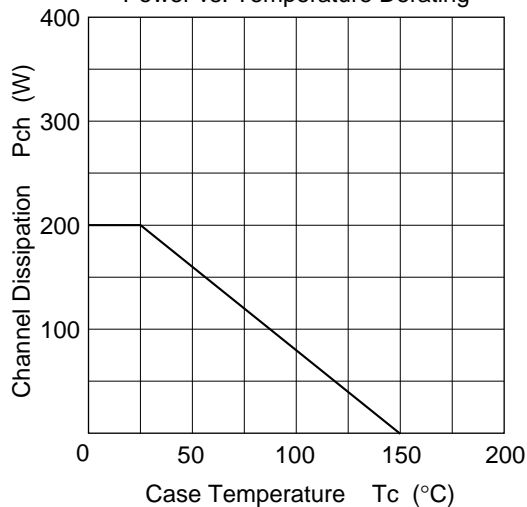
Electrical Characteristics (Ta = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test conditions |
|---|---------------|-----|------|-----|------|---|
| Drain to source breakdown voltage* ¹ | $V_{(BR)DSS}$ | 180 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0$ |
| Gate to source breakdown voltage* ¹ | $V_{(BR)GSS}$ | ±20 | — | — | V | $I_G = \pm 100 \mu\text{A}$, $V_{DS} = 0$ |
| Zero gate voltage drain current* ¹ | I_{DSS} | — | — | 1 | mA | $V_{DS} = 140 \text{ V}$, $V_{GS} = 0$ |
| Gate to source cutoff voltage* ¹ | $V_{GS(off)}$ | 0.5 | — | 2.0 | V | $I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$ |
| Drain to source cutoff voltage* ¹ | $V_{DS(on)}$ | — | 3.8 | 6.0 | V | $I_D = 4 \text{ A}$, $V_{GS} = 10 \text{ V}^{*2}$ |
| Forward transfer admittance* ¹ | $ y_{fs} $ | 0.9 | 1.25 | — | S | $I_D = 3 \text{ A}$, $V_{DS} = 20 \text{ V}^{*2}$ |
| Input capacitance* ¹ | Ciss | — | 440 | — | pF | $V_{GS} = 5 \text{ V}$, $V_{DS} = 0$ $f = 1 \text{ MHz}$ |
| Output capacitance* ¹ | Coss | — | 75 | — | pF | $V_{DS} = 50 \text{ V}$, $V_{GS} = 0$ $f = 1 \text{ MHz}$ |
| Reverse transfer capacitance* ¹ | Crss | — | 0.5 | — | pF | $V_{GD} = -50 \text{ V}$, $f = 1 \text{ MHz}$ |
| Output Power | Po | 180 | 220 | — | W | $V_{DS} = 80 \text{ V}$, $I_{DQ} = 0.2 \text{ A}$ |
| Drain Efficiency | η_D | — | 65 | — | % | $f = 190 \text{ MHz}$, $P_{in} = 10 \text{ W}$ |

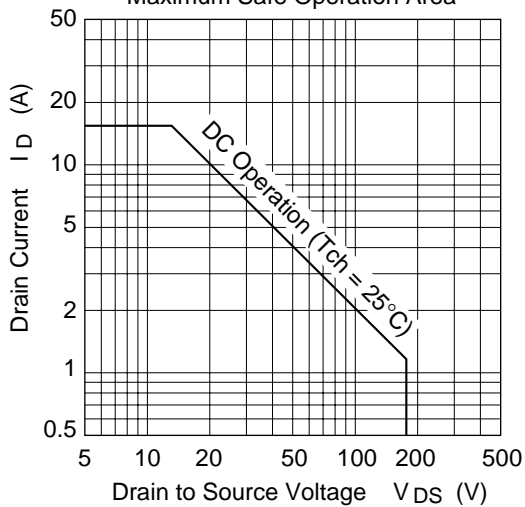
Notes: 1. Shows / unit FET

2. Pulse Test

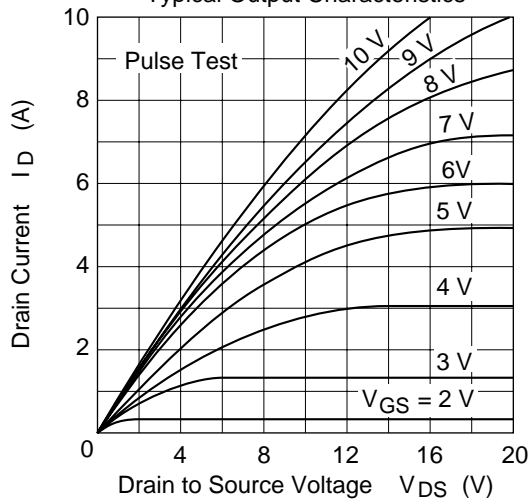
Power vs. Temperature Derating



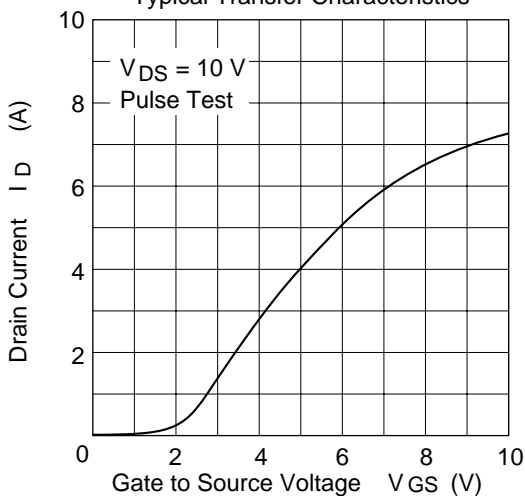
Maximum Safe Operation Area



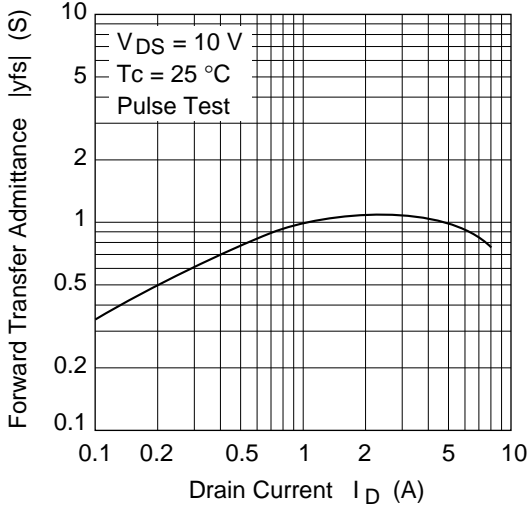
Typical Output Characteristics



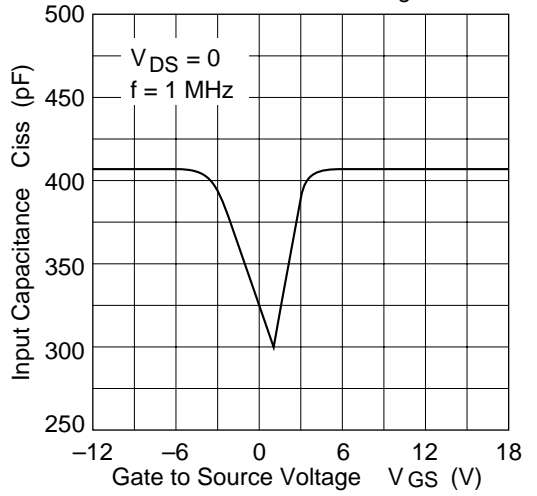
Typical Transfer Characteristics



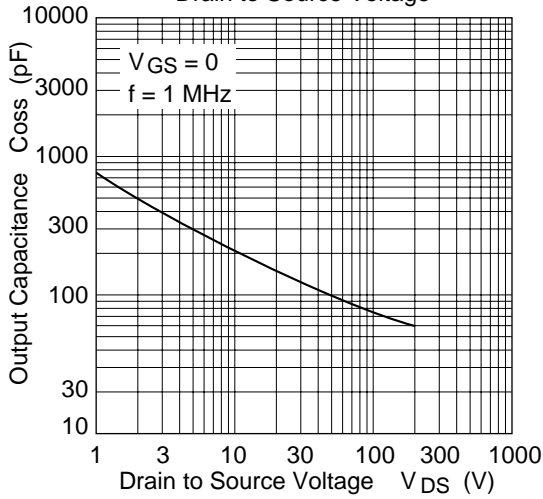
Forward Transfer Admittance vs. Drain Current



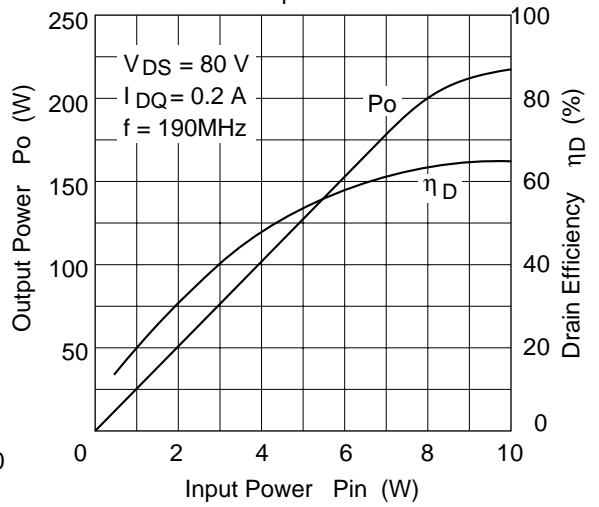
Input Capacitance vs. Gate to Source Voltage



Output Capacitance vs. Drain to Source Voltage

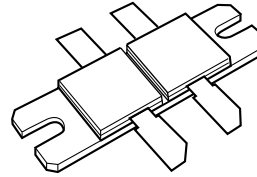
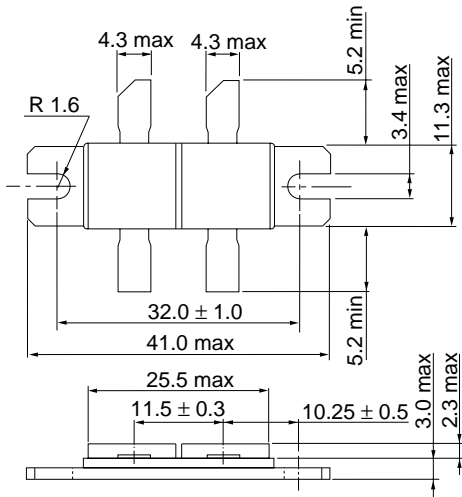


Output Power, Drain Efficiency vs. Input Power



Package Dimensions

Unit: mm



| | |
|--------------|--------|
| Hitachi Code | RFAK-B |
| EIAJ | — |
| JEDEC | — |

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